Temperature Dependence of Scaling Parameters in Anomalous and Nonlinear Hall Effects

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In the study of the anomalous Hall effect, the scaling relations between the anomalous Hall and longitudinal resistivities play the central role. The scaling parameters by definition are fixed as the scaling variable (longitudinal resistivity) changes. Contrary to this paradigm, we unveil that the electron-phonon scattering can result in apparent temperature-dependence of the scaling parameters when the longitudinal resistivity is tuned through temperature. An experimental approach is proposed to observe this temperature-dependence. We further show that this phenomenon also exists in the nonlinear Hall effect and helps identify experimentally the presence of the side-jump contribution besides the Berry-curvature dipole.

The anomalous Hall effect (AHE) [1] has been a fruitful topic of condensed matter physics, providing a paradigm widely-employed to understand related nonequilibrium phenomena such as spin and valley Hall effects [2,3] and spin-orbit torque [4]. In time-reversal broken multiband electronic systems with strong spin-orbit coupling, the AHE originates from both the momentum-space Berry curvature and carrier scattering off even scalar disorder without internal structure in spin space [5–7]. In experiments the scaling relations linking the anomalous Hall resistivity $\rho_{\text{AH}}$ to the longitudinal resistivity $\rho$ play the central role in identifying various contributions [8–18].

The well-established theory taking into account a given type of weak-potential static impurities [1,6,9,19] results in the scaling relation (henceforth the subscript “0” and “1” represent contributions from electron-impurity and electron-phonon scattering, respectively):

$$ -\rho_{\text{AH},0} = \alpha_0 \rho_0 + (c + c_0 + c_{00}) \rho_0^2, \quad (1) $$

where $\alpha_0$ arises from the conventional skew scattering [21], $c$ is the Berry-curvature contribution, $c_0$ results from the side-jump related to scattering-induced coordinate-shift [22,23], and $c_{00}$ incorporates scattering-induced contributions that are not related to the coordinate-shift but share the same scaling behavior as the side-jump one [5,20] (hereafter referred to as the side-jump-like contribution [24]). $\alpha_0$, $c$, $c_0$ and $c_{00}$ do not depend on the density of scatterers thus serve as scaling parameters, and $\rho_0$ tuned via changing the density of scatterers plays the role of a scaling variable. On the other hand, in many experiments the resistivity is tuned by changing temperature ($T$) [8,10,12,15–18]. In the case of electron-phonon (el-ph) scattering, most previous theoretical and experimental researches suggest the scaling relation [16,22,25,20]

$$ -\rho_{\text{AH},1} = (c + c_1 + c_{11}) \rho_0^2, \quad (2) $$

where the scaling parameters $c_1$ and $c_{11}$ are thought, according to the aforementioned characteristic of side-jump and side-jump-like contributions [16,22,20], to be independent of the density of phonons and thus of temperature. In the presence of both impurities and phonons, when assuming the Matthiessen’s rule $\rho_{xx} = \sum_{i=0,1} \rho_i$, a two-variable scaling based on the above two scalings reads [16] ($\rho_{xx} \gg \rho_{\text{AH}}$, $\sigma_{\text{AH}} \simeq -\rho_{\text{AH}}/\rho_{xx}^2$)

$$ \sigma_{\text{AH}} = \alpha_0 \rho_0^2 + c + \sum_{i=0,1} c_i \rho_i + \sum_{i,j=0,1} c_{ij} \rho_i \rho_j / \rho_{xx}^2, \quad (3a) $$

Here $c_1 + c_{01}$ represents the combined effect of carrier scatterings off impurities and phonons, and are also regarded to remain constant when the phonon density changes with temperature [16,18].

In this Letter we uncover that the above widely-accepted paradigm misses the physics that $c_1$ and $c_{10} + c_{01}$ can be strongly $T$-dependent as temperature drops below the high-$T$ classical equipartition regime where $\rho_1 \propto T$ [27]. In the two-dimensional (2D) massive Dirac model, Eq. (3a) is shown with all $c$’s given explicitly (detailed later) and reorganized into

$$ \sigma_{\text{AH}} - \alpha_0 \sigma_{xx}^2 / \sigma_0 = \beta + \beta' \sigma_{xx} / \sigma_0 + \beta'' (\sigma_{xx} / \sigma_0)^2, \quad (3b) $$

where $\sigma_0^{-1} = \rho_0$. The $T$-dependence of

$$ \beta(T) = c + c_1 (T) + c_{11} (T), $$
$$ \beta'(T) = c_0 - c_1 (T) + c_{01} (T) + c_{10} (T) - 2c_1 (T), $$
$$ \beta''(T) = c_0 + c_{11} (T) - c_{01} (T) - c_{10} (T), \quad (4) $$

are shown in Fig. 1, although they are believed to be $T$-independent in the conventional paradigm of the AHE [16,17]. Despite that the specific $T$-dependent forms of $\beta$’s depend on fine details of the model, the revealed possibility of the $T$-dependence of $c_1$, $c_{11}$ and $c_{10} + c_{01}$ is ubiquitous, as shown in the Supplemental Material [28]. The qualitative picture is simple: the side-jump and side-jump-like contributions are conventionally viewed as independent of scattering time for a given source of scattering [7,22,20], but in general they are just zeroth-order homogeneous terms of scattering time [30] (apparent in Eqs. (3) and (7)). In the equipartition regime the $T$-dependence of el-ph scattering times in the denominator and numerator of these zeroth-order homogeneous terms are the same ($T^{-1}$), and thereby drop out of $\beta$’s. While
at lower temperatures the bosonic nature of phonon occupation number makes the $T$-dependence irreducible.

This finding suggests that, the conventionally identified “scaling parameters” in Eqs. (2) – (3b) are in fact allowed to vary with temperature when fitting data. From a viewpoint of fundamental physics, scaling parameters by definition ought to be fixed as the scaling variable $\beta$. In 2D metallic systems with low carrier densities. When the temperature drops below the high-$T$ classical equipartition regime $T > T_{BG}$ where the phonon-limited resistivity is nearly linear in $T$, the $\beta$'s become $T$-dependent.

In the 2D massive Dirac model \[ \hat{H}_0 = v (\hat{\sigma}_x k_x + \hat{\sigma}_y k_y) + \Delta_0 \hat{\sigma}_z, \] \[ \hat{\sigma}_{x,y,z} \] are the Pauli matrices, $k$ is the wave-vector, $v > 0$ and $\Delta_0 > 0$ are model parameters. We consider the electron-doped case with Fermi energy $\epsilon_F > \Delta_0$. Since rigorous quantum field-theoretical considerations of the el-ph scattering in the AHE are very complicated, we employ for acoustic phonons the quasi-static treatment to establish a transparent picture. The quasi-static approximation is used in textbooks to show the low-$T$ power law $\rho_t \sim T^5$ for three-dimensional (3D) isotropic single-Fermi-surface systems. In a recent work on the phonon-induced side-jump anomalous Hall effect, the high-$T$ and low-$T$ asymptotic behaviors derived in this approximation are shown to be the same as those obtained without this approximation, and quantitative deviations only appear in the intermediate regime, which are by no means essential. In this approximation the quantum dynamical character of phonons is neglected, hence the el-ph scattering is treated as an elastic scattering process, with the plane-wave part of the lowest-Born-order scattering rate given by $W_{sk}^{ep} = \frac{2N_a}{v} |V_{sk}^{qo}|^2$. Here $U_{sk}^{q}$ is the plane-wave part (i.e., the part independent of the periodic amplitude $\hat{\sigma}_k$ of the Bloch wave) of the el-ph matrix element, $V$ is the volume (area in 2D) of the system, $N_a$ is the Bose occupation function for the phonon model with wave-vector $q$ and energy $\hbar \omega_q$, and the factor 2 accounts for the absorption and emission of phonons. The quantum zero-point motion is neglected, thus el-ph scatterings are all normal processes and $q = k' - k$. In comparison, for static impurities $W_{sk}^{el} = n_i |V_{sk}^{qo}|^2$, with $V_{sk}^{qo}$ the plane-wave part of the matrix element of the impurity potential. Hereafter the superscript “$e_i/ep$” means that the quantity is contributed by the electron-impurity/el-ph scattering alone.

The generalized Boltzmann transport theory incorporating virtual scattering processes induced by static or quasi-static disorder is employed. The relevant formulas involving not only on-shell (on the Fermi surface) but also off-shell (far away from the Fermi surface) Bloch states are presented in the Supplemental Material. In the presence of scalar quasi-static disorder, after some algebra the side-jump ($sj$) and side-jump-like ($sjl$) contributions to the anomalous Hall conductivity of model \[ \hat{H}_0 \] are obtained as \[ \sigma_{AH}^{sj} = \frac{e^2}{4\pi \hbar} \sin^2 \theta_F \cos \theta_F \left( \tau^{-1}_{tr} - \tau^{-1}_{i} \right) \tau_{tr}, \] and (henceforth we use the notation $\sigma_{AH}^{sjl} = \sigma_{AH}^{sj} + \sigma_{AH}^{sjl}$) \[ \sigma_{AH}^{sjl} = \frac{e^2}{64\pi \hbar} \sin^4 \theta_F \cos \theta_F \left( \tau^{-1}_{tr} - \tau^{-1}_{i} \right) \tau_{tr}^2, \] respectively. Here $\cos \theta_F = \Delta_0/\epsilon_F$, $\sin \theta_F = v k_F/\epsilon_F$. The $\tau_{tr}^{-1}$ is the value of the inverse transport relaxation time \[ \tau_{tr}^{-1}(k) = \frac{D_k}{\hbar} \int d\phi_{k'k} |\langle u_{k'}|u_k \rangle|^2 W_{k'k}(1 - \cos \phi_{k'k}) \] on the Fermi surface, and \[ \tau_{n}^{-1}(k) = \frac{D_k}{\hbar} \int d\phi_{k'k} W_{k'k} \cos (n \phi_{k'k}), \quad n = 0, 1, 2, \ldots \] where $D_k$ is the density of states, $\phi_{k'k}$ is angle between $k$ and $k'$, and $|u_k \rangle$ is the spinor eigenstate in the positive band. As will be shown later, $\sigma_{AH}^{sj}$ and $\sigma_{AH}^{sjl}$ reduce to the third and fourth terms on the right hand side of Eq. (3a), respectively. Hence $\sigma_{AH}^{sjl}$ is necessary to show the $T$-dependence of $\beta$ and $\beta'$ $\beta''$. In the Boltzmann theory $\sigma_{AH}^{sjl}$ arises from the antisymmetric part of
the third-Born-order scattering rate \(6, 8\), which contains two disorder lines that can be both noncrossed and crossed \(22\). Results from the noncrossed and crossed parts are quantitatively similar \(20, 39, 40\). These fine details on the treatment of disorder are not essential to the basic idea of showing that the \(T\)-dependence of \(g^2\), thus calculating the noncrossed part of \(\sigma_{\text{AH}}^\text{J,ei}\) alone as in Eq. \(7\) is sufficient in our study.

To obtain analytic results, we assume zero-range scalar impurities \((|V_{k\mathbf{k}}|^2 = V^2\) is a constant\), isotropic Debye phonons, and the deformation-potential el-ph coupling \(31\) for which a so-called el-ph coupling constant \(\gamma^2 = 2V^{-1} |U_{k\mathbf{k}}|^2 / \hbar \omega_q\) exists \(41\). Then

\[
W_{k\mathbf{k}} = W_{k\mathbf{k}}^\text{ei} + W_{k\mathbf{k}}^\text{ep} = n_i V_i^2 + g^2 k_B T \frac{z}{e^z - 1},
\]

where \(z = \hbar \omega_q / k_B T = \frac{q^2 T_B G}{k_T B_G}, \) and \(T_B G = h c_\text{s} 2 k_F / k_B\) \((c_\text{s}\) is the sound velocity) is the Bloch-Gruneisen temperature. Model results of \(\sigma_{\text{AH}}\) are obtained \(28\) according to \((\tau_{n} \rightarrow \tau_{n}^\text{ep})\) with \(W_{k\mathbf{k}}\) given by \(W_{k\mathbf{k}}^\text{ei/ep}\)

\[
\tau_n^{-1} \tau_{tr} = \left(\frac{\tau_n^{\text{ei}}}{\tau^{\text{ep}}} \right)^{-1} + \left(\frac{\tau_n^{\text{ep}}}{\tau_{tr}} \right)^{-1}, \quad n = 0, 1, 2...
\]

and shown in Fig. 2(a), where \(\eta = g^2 k_B T_B G / n_i V_i^2\) denotes the purity of system: larger \(\eta\) means smaller \(n_i\).

We first inspect the phonon-limited result for the pure system obtained by assuming \(n_i = 0\) in the beginning of the calculation, namely the dotted curve in Fig. 2(a). In the high-\(T\) limit \(W_{k\mathbf{k}}^\text{ep} = g^2 k_B T\) drops out of \(\tau_{tr}/\tau_n\), thus the latter coincides with that contributed by zero-range scalar impurities. In the low-\(T\) limit \(W_{k\mathbf{k}}^\text{ep} / k_B T\) is highly peaked at \(\phi_{k\mathbf{k}} = 0\), accordingly we prove the \(T\)-independent relation \(\left[\left(\frac{\tau_n^{\text{ei}}}{\tau_{tr}}\right)^{-1} - \left(\frac{\tau_n^{\text{ep}}}{\tau_{tr}}\right)^{-1}\right] \tau_{tr}^{\text{ep}} = 1 + 2n\), which also holds for scalar impurity scattering of the long-range limit. Thereby, the phonon-limited \(\sigma_{\text{AH}}^\text{J}\) in the high-\(T\) \((\text{high-}T)\) limit are the same as the scalar impurity-limited one in the zero-range \(30\) (long-range \(20\)) limit.

For finite \(n_i\), at high temperatures \(\sigma_{\text{AH}}^\text{J}\) is still the same as that contributed by zero-range scalar impurities since \(W = n_i V_i^2 + g^2 k_B T\) drops out of \(\tau_{tr}/\tau_n\). This feature can extend to the lower boundary \(T_L\) of the equipartition regime where \(\rho_1 \propto T\). Below \(T_L\), \(W_{k\mathbf{k}}^\text{ep}\) is not proportional to \(T\) thus \(\sigma_{\text{AH}}^\text{J}\) becomes \(T\)-dependent apparent if \(W_{k\mathbf{k}}^\text{ep}(T_L) \gg W_{k\mathbf{k}}^\text{ei}\). In our model case \(T_L \approx T_B G\), thus \(\eta \approx \tau_0^{\text{ei}} / \tau_0^{\text{ep}}(T_L) = \tau_{tr}/\tau_{tr}^{\text{ep}}(T_L)\), i.e.,

\[
\eta \approx \frac{\rho_1(T_L)}{\rho_0} = \frac{\rho_{xx}(T_L)}{\rho_0}.
\]

To understand the low-\(T\) behavior of \(\sigma_{\text{AH}}^\text{J}\), we first note that \((n_i = 0, T = 0)\) is a singular point of \(\sigma_{\text{AH}}^\text{J}(n_i, T)\) in systems with zero-range impurities: the limits \(n_i \to 0\) and \(T \to 0\) do not commute. While \(\lim_{T \to 0} \sigma_{\text{AH}}^\text{J}(n_i, T) = \sigma_{\text{AH}}^\text{J,ei}\) is the \(n_i\)-independent contribution from zero-range impurities \(4\), \(\lim_{T \to 0} \sigma_{\text{AH}}(n_i, T) = \sigma_{\text{AH}}^{\text{J,ei}}(T \to 0)\) is the phonon-limited contribution in the low-\(T\) limit, which is equal to that from long-range impurities. In realistic systems \(n_i \neq 0\) thus the low-\(T\)-limit value of \(\sigma_{\text{AH}}\) is \(\sigma_{\text{AH}}^\text{J,ei}\). Whereas \(\sigma_{\text{AH}}^{\text{J,ei}}\) still describes the behavior at not too low temperatures, especially in high-purity systems, as shown in Fig. 2(a). Thereby the non-monotonic \(T\)-dependence of \(\sigma_{\text{AH}}\) appears in the intermediate regime.

![Figure 2](image-url)

**FIG. 2.** Temperature-dependence of (a) \(\sigma_{\text{AH}}\) and of (b) \(\sigma_{\text{AH}}\) in the presence of both zero-range scalar impurities and acoustic phonons. Larger values of the parameter \(\eta = g^2 k_B T_B G / n_i V_i^2\) correspond to higher impurity density. The dotted curve in (a) is the phonon-limited result, i.e., \(c_1 + c_1^2\). The dashed curves in (a) and (b) are obtained by assuming the scaling relation \(15\) in the presence of both scattering sources.

Now we take into account the skew scattering \(\langle \text{sk} \rangle\) from the third-order non-Gaussian impurity correlator \(n_i V_i^3\) of zero-range scalar impurities \(3\) \(30\):

\[
\sigma_{\text{AH}}^\text{sk} = \frac{e^2}{16\pi^2} \sin^4 \theta_F \left(\frac{\tau_{tr}}{\tau_0}\right)^2 D_F V_i \Delta_0 \tau_{tr}^{\text{ei}} / h,
\]

where \(D_F\) is the density of states on the Fermi surface. In the weak scattering regime \(D_F V_i \ll 1\) and \(\Delta_0 \tau_{tr}^{\text{ei}} / h \gg 1\). In Fig. 2(b) we take \(D_F V_i = 10^{-3}, \Delta_0 \tau_{tr}^{\text{ei}} / h = 10^{+2}\) for \(\eta = 3 \times 10^j\) \((j = 0, 1, 2)\), and \(\Delta_0 \tau_{tr}^{\text{ei}} / h = 5 \times 10^2\) for \(\eta = 1500\) (\(V_i\) is fixed when \(n_i\) is tuned).

The model result \(\sigma_{\text{AH}} - c = \sigma_{\text{AH}} - \sigma_{\text{AH}} = \sum \alpha_n \tau_{n-1}^{\text{ei}} - \tau_{tr} + \sum \alpha_n \beta_n^{\text{ei}} - n \tau_{tr}^{\text{ei}} (a_n^3 + b_n^{3})\) can be cast into Eq. \(31\), where \(\sigma_{\text{AH}} = \alpha_0 \rho_{xx} \rho_0\) and \(\rho_{0(1)} = \rho_{xx} \tau_{tr} / \tau_{tr(\text{ei})}\). The impurity-determined coefficients \(\alpha_0 = D_F V_i^{\text{ei} / \tau_{tr}^{\text{ei}}}\), \(c_0 = \sigma_{\text{AH}}^{\text{J,ei}} = \sum \alpha_n \tau_{tr}^{\text{ei} / \tau_{tr}^{\text{ei}}}\).
and $c_{00} = \sigma_{AH}^{sij,ei} = \sum_{n, n'} b_{nn'}^{ij} (\tau_r^{ei} / \tau_r^{ei})^2 / (\tau_r^{ei} + \tau_r^{ei})$ are independent of $n$. While the phonon-related coefficients, i.e.,

$$c_1 = \sigma_{AH}^{sij,ep} = \sum_n \sigma_n^{sij,ep} / \tau_r^{ep}, \quad c_{11} = \sigma_{AH}^{sij,ep} = \sum_{nn'} b_{nn'}^{ij} (\tau_r^{ep} / \tau_r^{ep})^2,$$

$$c_{01} + c_{10} = \sum_{nn'} b_{nn'}^{ij} \left( \frac{\tau_r^{ei}}{\tau_r^{ei}} + \frac{\tau_r^{ep}}{\tau_r^{ep}} \right), \quad (14)$$

are $T$-dependent below the high-$T$ equipartition regime, leading to the $T$-dependence in Fig. 1. This implies that Eq. 3 can not be theoretically viewed as a scaling relation, since the conventionally identified “scaling parameters” $c_1 + c_{11}$ changes as $T_1$ varies with temperature. Equations (5a) and (3b) suffer from the same situation.

If the el-ph scattering related $c_1$’s took $T$-independent values, as those in the high-$T$ regime: $c_1 = c_0$ and $c_{ij} = c_{00}$, the scaling relation would hold and read

$$\sigma_{AH} = \alpha_0 \sigma_0^{-1} \sigma_x^2 + c + c_0 + c_{00}. \quad (15)$$

The deviation of $\sigma_{AH}$ is apparent only in high-purity systems (dashed curves in Fig. 2(b)), as indicated by Eq. 5a when $\rho_0 \gg \rho_1$. This provides a clue to understand the approximate validity of scaling relations in previous tuning-$T$ experiments on moderately dirty samples (smaller $n$). By contrast, it is worthwhile to emphasize that in Eq. 3b the $\beta$’s do not depend on $\rho_0$, thus their $T$-dependence shows up irrespective of the sample quality.

In Fig. 1 $\beta'$ and $\beta''$ converge to zero in the high-$T$ regime since $c_1 = c_0$ and $c_{ij} = c_{00}$ in this regime. This is not necessarily to be true when the approximations concerning el-ph scattering made in the model calculation are invalid, especially when the el-ph Umklapp process is important. This may be the case in some 3D metals with high carrier density, where large-angle el-ph scatterings happen via Umklapp processes.

Next we propose an experimental procedure to observe the predicted $T$-dependence of $\beta$’s, based on the recently developed thin film approach in the AHE study 15,17. In this approach the effective impurity density can be continuously manipulated by tuning the thickness of single crystalline magnetic thin films, meanwhile the electronic band structure does not change in the thickness range. Utilizing this approach one can limit the scattering of carriers to two sources — interface roughness and phonons (the Curie temperature is assumed to be much higher than the Debye temperature, which is the case of Fe and Co), and realize independent control of the densities of static impurities and phonons through the film thickness and sample temperature, respectively.

In the low-$T$ limit $\sigma_x = \sigma_0$, and Eq. 3b reduces to the linear scaling $\sigma_{AH} = \alpha_0 \sigma_0 + c + c_0 + c_{00}$, thereby $\alpha_0$ can be extracted by tuning $\sigma_0$ through the film thickness. The experimental confirmation of this linear scaling is necessary to ensure that there involves only one dominant type of static impurity [30] in the experimental range. Because in Eq. 3b the $\beta$’s are still scaling parameters that remain unchanged when only the film thickness is tuned, one can plot $(\sigma_{AH} - \alpha_0 \sigma_0^{-1} \sigma_x^2)$ versus $\sigma_0^{-1} \sigma_x^2$ through tuning the film thickness for every chosen fixed temperature. One can then extract the $\beta$’s for different temperatures from the high-$T$ equipartition regime $T > T_L$ (experiments in common 3D metals often show $T_L \approx T_D / 3$ as the lower boundary of the $\rho_1 \propto T$ regime, with $T_D$ the Debye temperature 43,44) down to the low-$T$ residual-resistivity regime. The $T$-variation curves of $\beta$’s are thus obtained. At $T > T_L$ the predicted $T$-independent high-$T$ value of $\beta$’s can be determined first, whereas their $T$-dependence can be observed as the temperature drops below $T_L$.

Finally we extend the discussion to the nonlinear Hall effect (NLHE) — a second-order Hall response to the electric field in non-magnetic systems with inversion breaking 45,50. The systematic Boltzmann analysis of this effect up to the linear order of scattering time 51-54 incorporates the Berry-curvature dipole (bcd) mechanism 45,47,49,55 and the nonlinear generalizations of the side-jump, side-jump-like and skew scattering contributions 56. Equation 3 has been extended to the NLHE in the dc limit as $V_y^N / (V_x^L)^2 = C + A_0 \rho_0 / \rho_{xx}^2 + \sum_{i=0,1} (C_i \rho_i / \rho_{xx} + C_j \rho_j / \rho_{yy}^2)$. Here $V_y^N$ and $V_x^L$ are the nonlinear Hall and linear longitudinal voltage, respectively. $V_y^N / (V_x^L)^2 = \chi_{yxx} \rho_{xx}$ with $\chi_{yxx}$ the second-order response coefficient of the NLHE. Equivalently 54,

$$V_y^N / (V_x^L)^2 = A_0 \sigma_0^2 / \sigma_0 = B + B' \sigma_x / \sigma_0 + B'' \sigma_x / \sigma_0, \quad (16)$$

where $B = C + C_1 + C_1$, $B' = C_0 - C_1 + C_0 + C_1 - 2C_1$ and $B'' = C_00 - C_11 - C_00 - C_0$. Note that all $C$’s are zeroth-order homogeneous terms of scattering time 54. In particular, $C = \chi_{yxx} \rho_{xx}$; $C_0(1) = \chi_{yxx} \rho(1)$ and $C_{00}(11) = \chi_{yxx} \rho(1)$. Following the conventional paradigm of the AHE 16,17, in previous understanding Eq. 16 is viewed as a scaling relation when tuning temperature, and the $B$’s are believed to be $T$-independent.

According to our work on the AHE, however, it is apparent that the $B$’s are in general $T$-dependent. An experimental procedure similar to the aforementioned one in the case of the AHE can be applied to verify this idea. The $T$-dependence of the $B$’s arises from that of the phonon-related side-jump and side-jump-like terms, e.g., $C_1$ and $C_11$, as in the AHE. The $T$-dependence of el-ph scattering times in the denominator and numerator of these zeroth-order homogeneous terms are the same ($T^{-1}$) in the high-$T$ regime where $\rho_1 \propto T$, and thereby drop out, leading to $T$-independent $B$’s. While at lower temperatures, the bosonic nature of the phonon occupation makes the $T$-dependence irreducible even in the zeroth-order homogeneous terms. Illustration of this $T$-
dependence in the NLHE of the 2D tilted massive Dirac model is presented in Ref. 28.

In a recent experiment on the NLHE in bilayer WTe$_2$ [17], only the Berry-curvature dipole mechanism was observed. Whereas in another experiment on few-layer WTe$_2$ [16], a scaling taking the form of [15] ($\sigma_{AH} \rightarrow V^N_y / (V^L_y)^2$) was observed in tuning-\(T\) measurements, indicating the presence of the skew scattering. Since the experimental system is dirty ($\eta < 1$), the emergence of scaling in practice is reasonable. In order to further investigate the relevance of the side-jump (-like) contribution besides the Berry-curvature dipole, a possible route suggested by our results is to observe the \(T\)-dependence of \(B\) in Eq. (16) by using multi-step WTe$_2$ sample through the above described experimental approach.

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[24] In the review paper [1] \(\sigma_{00}\) is also included into the category of side-jump, whereas in some other papers (e.g., Refs. [6, 20]) \(\sigma_{00}\) is not called side-jump. The present terminology can be viewed as a compromise between different opinions in the community.

[28] See Supplemental Material for calculation details of Figs. 1 and 2, the derivation of Eqs. (3) and (7), model-independent analysis of the \(T\)-dependence of \(\beta\)'s in the AHE, and analyses of the \(T\)-dependence of \(B\)'s in the NLHE of the 2D tilted massive Dirac model.
[36] Neglecting the zero-point motion is also necessary for the correct low-\(T\) asymptotic behavior in the quasi-static approximation, as pointed out by Ziman (Ref. 27).